

AMENDMENTS TO THE SPECIFICATION

Please replace the title with the following:

METHOD OF FORMING A FLIP CHIP

Please replace Paragraph [0001] with the following paragraph rewritten in amendment format:

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application is a divisional of United States Patent Application No. 10/136,119 filed on ~~May 2, 2002~~May 1, 2004, which is hereby incorporated by reference in its entirety. The content of co-pending U.S. application No. 10/051,965, filed January 16, 2002, is also incorporated by reference in its entirety.

Please replace Paragraph [0005] with the following paragraph rewritten in amendment format:

[0005] A method of forming a flip chip assembly is provided comprising a device
comprises providing a semiconductor die having a core area and a substrate. The
~~semiconductor die has a core area and a periphery area. The periphery area includes~~
~~an electrostatic discharge (ESD) structure. The semiconductor die includes and~~
~~includes at least one power conductor, to supply power between the core area and the~~
~~periphery. The periphery includes an ESD structure. A substrate having a source of~~
~~power is provided. The substrate is coupled to the semiconductor die via a plurality of~~
~~electrically conductive bumps. A first connection circuit is located within the~~

semiconductor die core area to couple power between the substrate and the semiconductor die power conductor. ~~An electrically conductive bump provides a connection between the first connection circuit and the substrate.~~ The ESD structure is electrically circuit is located outside of the semiconductor die core area and is coupled to the first connection circuit. The first connection circuit is electrically coupled to the substrate via a conductive bump.

Please add the following paragraphs:

[0005.1] In other features, the first connection circuit is a first under ball metallization (UBM). A second UBM is located over the ESD structure. The first UBM is electrically coupled to the second UBM on the substrate.

[0005.2] In other features, a second UBM is located over the ESD structure. The first UBM is electrically coupled to the second UBM on the semiconductor die. The semiconductor die further comprises a redistribution layer. The first UBM is electrically coupled to the second UBM on the redistribution layer.

[0005.3] In still other features, the semiconductor die includes a metallization side and an opposite side. The metallization side is electrically coupled to the substrate. The opposite side of the semiconductor die is thermally coupled to a heat sink. The substrate is electrically coupled to a first surface of a package substrate via a plurality of bond wires. The opposite side of the semiconductor die is adhesively bonded to the heat sink.

Please add the following paragraph:

[0011.1] Figure 6 is a flowchart illustrating steps for forming a flip chip assembly.

Please amend the Abstract section of the specification as rewritten in amendment format.

A method of forming a flip chip device comprises providing assembly comprising a semiconductor die having a core area and a periphery area. The periphery area includes an electrostatic discharge ESD structure. The semiconductor die including includes at least one power conductor, ~~to supply power between the core area and the periphery.~~ A substrate ~~is having a source of power is provided.~~ coupled to the semiconductor die via a plurality of electrically conductive bumps. A first connection circuit is located within the semiconductor die core area to couple power between the substrate and the semiconductor die power conductor. ~~An~~ The ESD structure is electrically coupled to conductive bump provides a connection between the first connection circuit and the substrate. The ESD structure ~~is coupled to the first connection circuit~~ is electrically coupled to the substrate via a conductive bump.